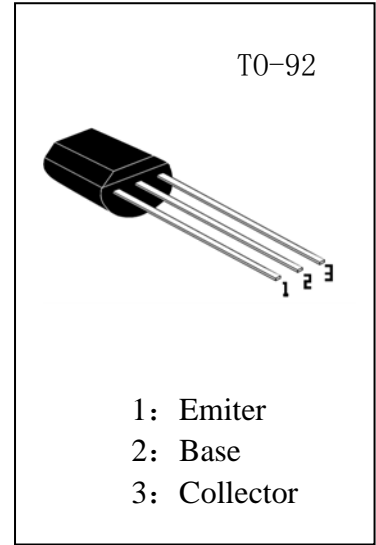


低压低噪晶体管

- 集电极电流 $I_c = -100\text{mA}$
- 耗散功率 $P_c = 450\text{mW}$
- 与 S9015 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	50	V
Collector-Emitter Voltage	V_{ceo}	45	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c	100	mA
Collector Dissipation	P_c	450	m W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$



电性能(Electrical Characteristic) $T_a = 25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c = 100\mu\text{A}$ $I_e = 0$	50			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c = 1\text{mA}$ $I_b = 0$	45			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e = 100\mu\text{A}$ $I_c = 0$	5			V
I_{cbo}	Collector Cutoff Current	$V_{cb} = 50\text{V}$, $I_e = 0$			50	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb} = 5\text{V}$, $I_c = 0$			50	nA
I_{ceo}	Collector Cutoff Current	$V_{ce} = 45\text{V}$, $I_b = 0$			15	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c = 100\text{mA}$, $I_b = 5\text{mA}$		0.14	0.3	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c = 100\text{mA}$, $I_b = 5\text{mA}$		0.84	1.0	V
$V_{be(on)}$	Base-Emitter On Voltage	$V_{ce} = 5\text{V}$, $I_c = 2\text{mA}$	0.58	0.6	0.7	V
H_{fe}	DC Current Gain	$V_{ce} = 5\text{V}$, $I_c = 1\text{mA}$	60		1000	
C_{ob}	Output Capacitance	$V_{cb} = 10\text{V}$, $I_e = 0$, $f = 1\text{MHz}$		2.2	3.5	PF
f_T	Current Gain-Bandwidth product	$V_{ce} = 5\text{V}$, $I_c = 10\text{mA}$	150	270		MHz
NF	Noise Figure	$V_{ce} = 5\text{V}$, $I_c = 0.2\text{mA}$ $f = 1\text{KHz}$, $R_s = 2\text{K}\Omega$		0.9	10	dB

Class	A	B		C		D	
H_{fe}	60-100	100-200	200-300	300-400	400-500	500-600	600-1000